

SEMICONDUCTOR

# **BCW33**

# **NPN General Purpose Amplifier**

- This device is designed for general purpose applications at collector currents to 300mA.
- Sourced from process 07.



1. Base 2. Emitter 3. Collector

# Absolute Maximum Ratings \* T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
CEO	Collector-Emitter Voltage	32	V
СВО	Collector-Base Voltage	32	V
EBO	Emitter-Base Voltage	5.0	V
0	Collector current (DC)	500	mA
J, T <sub>sta</sub>	Operating and Storage Junction Temperature Range	-55 ~ +150	°C

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

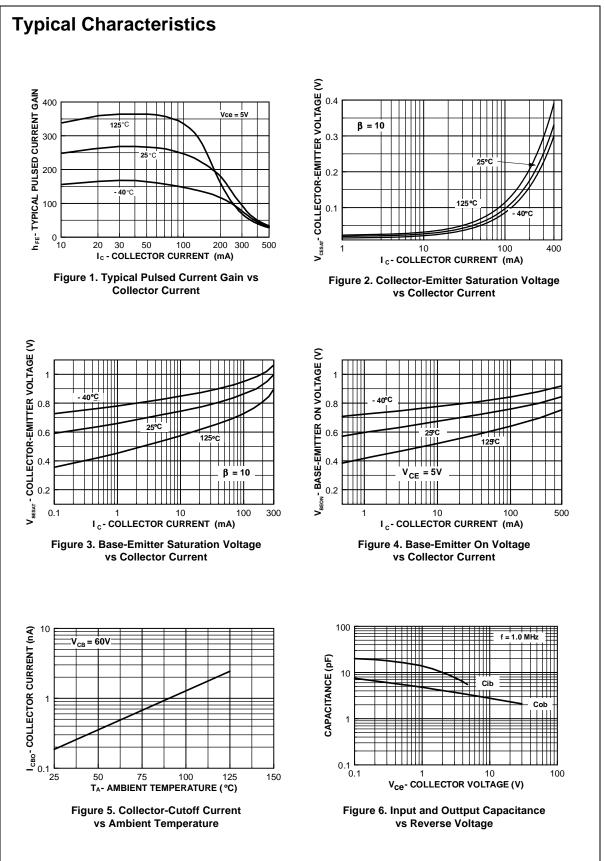
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Charact	eristics	·			•	
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 2.0 {\rm mA}, I_{\rm B} = 0$	32			V
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 \mu {\rm A}, \ I_{\rm B} = 0$	32			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm C} = 10\mu {\rm A}, I_{\rm C} = 0$	5.0			V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 32V, I_E = 0$ $V_{CB} = 32V, I_E = 0, T_A = 100^{\circ}C$			100 10	nA μA
On Charact	eristics					
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 2.0mA, V <sub>CE</sub> = 5.0V	420		800	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0.5 {\rm mA}$			0.25	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_{C} = 2.0 \text{mA}, V_{CE} = 5.0 \text{V}$	0.55		0.7	V
Small Signa	al Characteristics					
f <sub>T</sub>	Current Gain Bandwidth Product	I <sub>C</sub> = 2.0mA, V <sub>CE</sub> = 5.0V f = 35MHz	200			
C <sub>obo</sub>	Output Capacitance	$V_{CB} = 10V, I_E = 0, f = 1.0MHz$			4.0	pF
NF	Noise Figure	$I_{C} = 0.2$ mA, $V_{CE} = 5.0V$ R <sub>S</sub> = 2.0k $\Omega$ , f = 1.0kHz B <sub>W</sub> = 200Hz			10	dB

# Thermal Characteristics TA=25°C unless otherwise noted

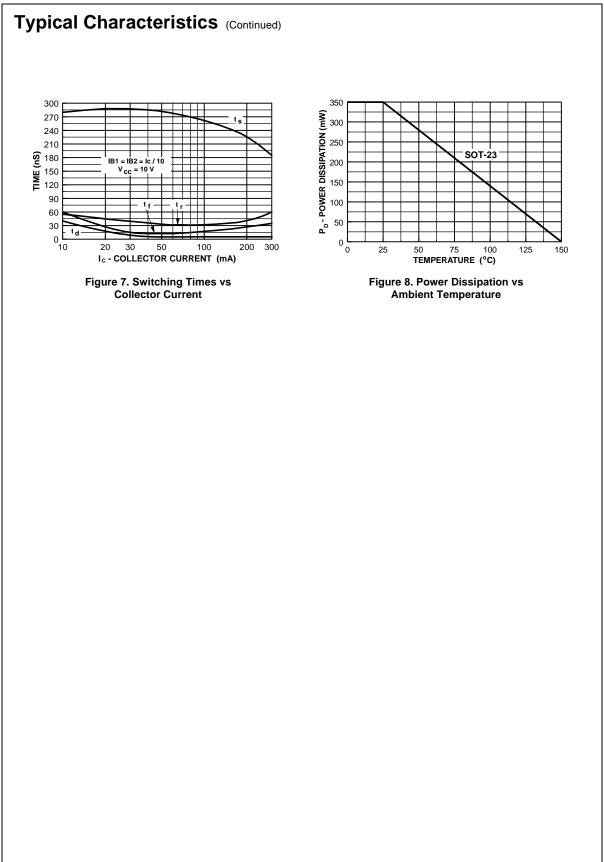
Symbol	Parameter	Max.	Units
PD	Total Device Dissipation	350	mW
-	Derate above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W
	FR-4PCB 40mm $\times$ 40mm $\times$ 1.5mm		

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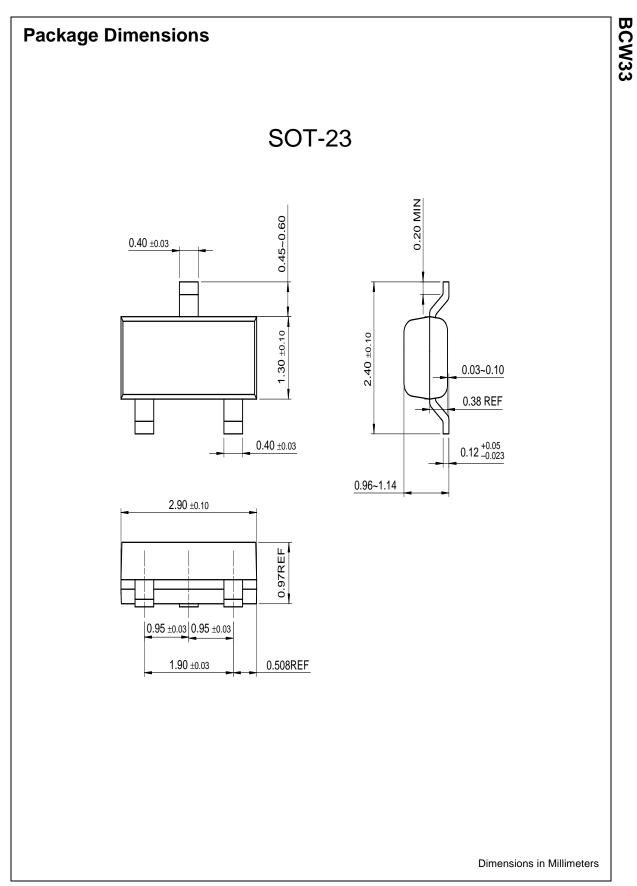
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